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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Application Number 09/986,332
 Confirmation Number 5542
 Filing Date November 8, 2001
 First Named Inventor KIYOKU, HIROYUKI
 Art Unit 1765
 Examiner Name Anderson, Matthew A.
 Attorney Docket Number Q66212

Sheet 1 of 1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
MAA		US 5,620,557	A	04-15-1997	Katsuhide MANABE et al.
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Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁴
		Country Code ³	Number ⁴	Kind Code ² (if known)			
MAA		JP	7-165498		06-27-1995	Toyoda Gosei Co. LTD.	Abstract + JPO Translation
MAA		JP	7-202265		08-04-1995	Mitsubishi Cable Ind. LTD.	Abstract + JPO Translation + US 5620557

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁴

Examiner Signature

Matthew Anderson

Date Considered

6/7/04

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Form PTO-1449 (Rev. 2-32)		U.S. Department of Commerce Patent & Trademark Office		Atty. Docket No. Q66212		Serial No.: Confirmation No.: To be Assigned	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				Applicant: Hiroyuki KIYOKU, et al.			
				Filing Date: 11/8/2001		Group: 1765	

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EXAMINER: <i>Matthew Chiles</i>	DATE CONSIDERED: <i>6/08/04</i>
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				Filing Date: 11/8/2001	Group: 1765
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